



30V NPN MEDIUM POWER LOW SATURATION TRANSISTOR IN SOT223

Features

- BV_{CEO} > 30V
- I_C = 7A Continuous Collector Current
- I_{CM} = 20A Peak Pulse Current
- Low Saturation Voltage V_{CE(SAT)} < 50mV Max @ 1A
- R_{SAT} = 28mΩ @ 6.5A for Low Equivalent On-Resistance
- hFE Specified up to 20A for High Gain Hold Up
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

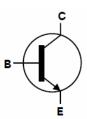
- Case: SOT223
- Case Material: Molded Plastic. "Green" Molding Compound.
 UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads. Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.112 grams (Approximate)

Applications

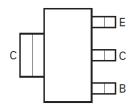
- DC-DC Converters
- MOSFET Gate Drivers
- Charging Circuits
- Power Switches
- Motor Control



Top View



Device Schematic



Pin-Out Top View

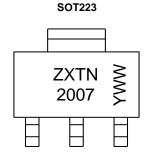
Ordering Information (Note 4)

Part Number	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
ZXTN2007GTA	ZXTN2007	7	12	1.000

Notes:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



ZXTN 2007 = Product Type Marking Code YWW = Date Code Marking Y or \overline{Y} = Last Digit of Year (ex: 5 = 2015) WW or $\overline{W}W$ = Week Code (01 - 53)



Absolute Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	80	V
Collector-Emitter Voltage	V _{CEO}	30	V
Emitter-Base Voltage	V _{EBO}	7	V
Continuous Collector Current	Ic	7	A
Peak Pulse Current	I _{CM}	20	A

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Power Dissipation	(Note 5)	D	3.0 24	W
Linear Derating Factor	(Note 6)	P _D	1.6 12.8	mW/°C
Thermal Desistance, Junction to Ambient	(Note 5)	$R_{\theta JA}$	42	
Thermal Resistance, Junction to Ambient	(Note 6)	$R_{\theta JA}$	78	°C/W
Thermal Resistance, Junction to Lead	(Note 7)	R _{0JL}	8.8	
Operating and Storage Temperature Range		T _{J,} T _{STG}	-55 to +150	°C

ESD Ratings (Note 8)

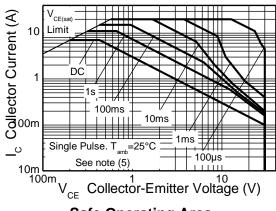
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge – Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge – Machine Model	ESD MM	400	V	С

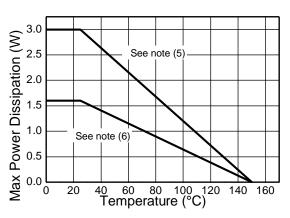
Notes:

- 5. For a device mounted with the collector lead on 52mm x 52mm 2oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in steady-state.
- 6. Same as Note 5, except the device is mounted on 25mm x 25mm 1oz copper.
- 7. Thermal resistance from junction to solder-point (at the end of the collector lead).
- 8. Refer to JEDEC specification JESD22-A114 and JESD22-A115.



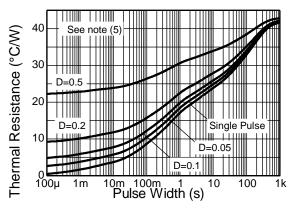
Thermal Characteristics and Derating Information

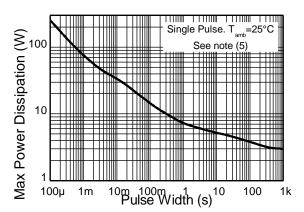




Safe Operating Area

Derating Curve





Transient Thermal Impedance

Pulse Power Dissipation



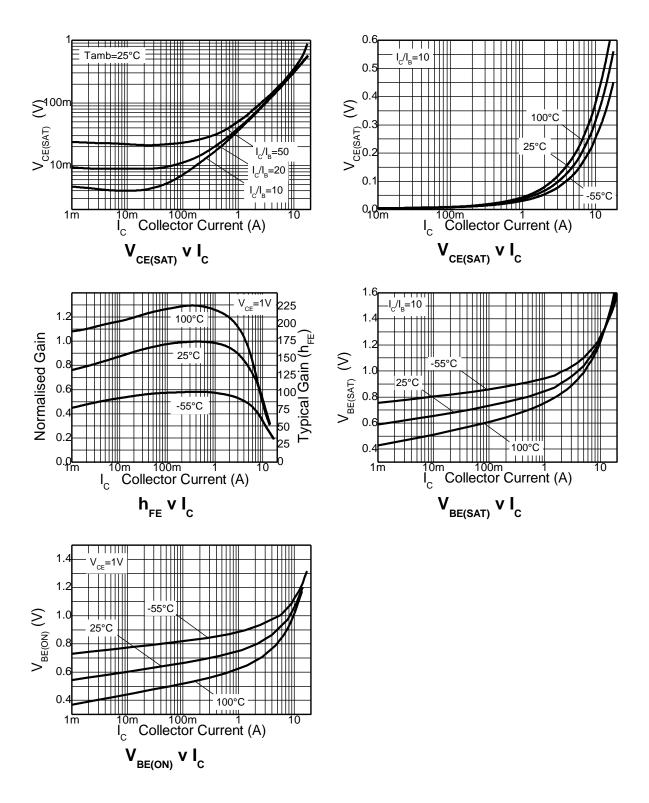
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	80	125	_	V	I _C = 100μA
Collector-Emitter Breakdown Voltage	BV _{CER}	80	125	_	V	$I_C = 1\mu A$, RB $\leq 1k\Omega$
Collector-Emitter Breakdown Voltage (Note 9)	BV _{CEO}	30	40	_	V	I _C = 10mA
Emitter-Base Breakdown Voltage	BV _{EBO}	7	8.1	_	V	I _E = 100μA
Collector Cutoff Current	I _{CBO}	_	< 1	50	nA	V _{CB} = 70V
		_		0.5	μA	$V_{CB} = 70V, T_A = +100^{\circ}C$
Collector Cutoff Current	I _{CER} R≤1kΩ	_	< 1 —	100 0.5	nΑ μΑ	V _{CB} = 70V V _{CB} = 70V, T _A = +100°C
Emitter Cutoff Current	I _{EBO}		< 1	10	nA	V _{EB} = 6V
Collector-Emitter Saturation Voltage (Note 9)	V _{CE(SAT)}	_	25 35 50	35 50 65	mV	I _C = 500mA, I _B = 20mA I _C = 1A, I _B = 100mA I _C = 1A, I _B = 20mA
<u> </u>	* OL(GAT)		100 185	125 220		$I_C = 2A$, $I_B = 20mA$ $I_C = 6.5A$, $I_B = 300mA$
Base-Emitter Saturation Voltage (Note 9)	V _{BE(SAT)}	_	1.03	1.13	V	$I_C = 6.5A$, $I_B = 150mA$
Base-Emitter Turn-On Voltage (Note 9)	V _{BE(ON)}	_	0.92	1	V	$I_C = 6.5A, V_{CE} = 1V$
DC Current Gain (Note 9)	h _{FE}	100 100 100 20	175 200 150 30	300	_	$\begin{split} I_{C} &= 10 \text{mA}, \ V_{CE} = 1 \text{V} \\ I_{C} &= 1 \text{A}, \ V_{CE} = 1 \text{V} \\ I_{C} &= 7 \text{A}, \ V_{CE} = 1 \text{V} \\ I_{C} &= 20 \text{A}, \ V_{CE} = 1 \text{V} \end{split}$
Transition Frequency	f⊤	_	140	_	MHz	$V_{CE} = 10V, I_{C} = 100mA,$ f = 50MHz
Output Capacitance (Note 9)	C _{OBO}	_	48	_	pF	V _{CB} = 10V, f = 1MHz
Cuitching Times	ton	_	37	_	20	$V_{CC} = 10V, I_C = 1A,$
Switching Times	toff	_	425	_	ns	$I_{B1} = -I_{B2} = 100 \text{mA}$

Note: 9. Measured under pulsed conditions. Pulse width \leq 300 μ s. Duty cycle \leq 2%.



Typical Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

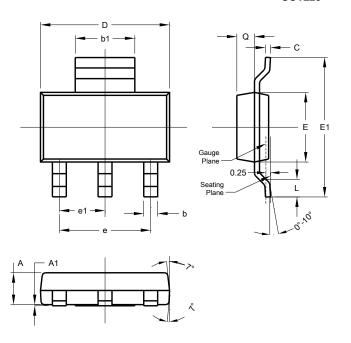




Package Outline Dimensions

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.

SOT223

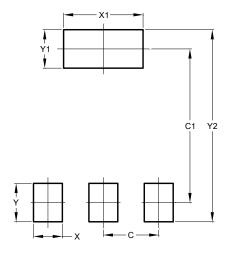


SOT223					
Dim	Min	Max	Тур		
Α	1.55	1.65	1.60		
A1	0.010	0.15	0.05		
b	0.60	0.80	0.70		
b1	2.90	3.10	3.00		
С	0.20	0.30	0.25		
D	6.45	6.55	6.50		
Е	3.45	3.55	3.50		
E1	6.90	7.10	7.00		
е	_	_	4.60		
e1	_	_	2.30		
L	0.85	1.05	0.95		
Q	0.84	0.94	0.89		
All Dimensions in mm					

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.

SOT223



Dimensions	Value (in mm)
С	2.30
C1	6.40
Χ	1.20
X1	3.30
Υ	1.60
Y1	1.60
C2	8.00



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